Silicon PNP Power Transistors 2SB536

DESCRIPTION

- With TO-220C package
- Complement to type 2SD381
- Low collector saturation voltage

APPLICATIONS

- Audio frequency power amplifier
- Low speed power switching

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

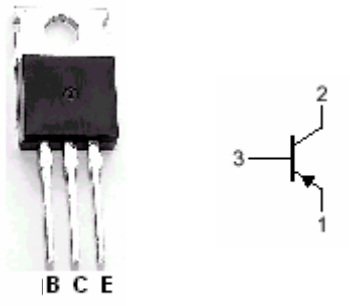

Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-130	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-1.5	A
I_{CM}	Collector current-peak		-3.0	A
I_B	Base current		-0.3	A
P_T	Total power dissipation	T_a=25℃	1.5	W
		T_C=25℃	20	
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-50~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-10mA; I_B=0	-120			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-1A; I_B=-0.1A			-2.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-1A; I_B=-0.1A			-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-120V; I_E=0			-1.0	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-3V; I_C=0			-1.0	μA
h_{FE-1}	DC current gain	I_C=-5mA ; V_{CE}=-5V	25			
h_{FE-2}	DC current gain	I_C=-0.3A ; V_{CE}=-5V	40		250	
C_{OB}	Output capacitance	I_E=0 ; V_{CB}=-10V; f=1MHz		35		pF
f_T	Transition frequency	I_C=-0.1A ; V_{CE}=-5V		40		MHz

◆ **h_{FE-2} Classifications**

N	M	L	K
40-80	60-120	80-160	120-250

PACKAGE OUTLINE

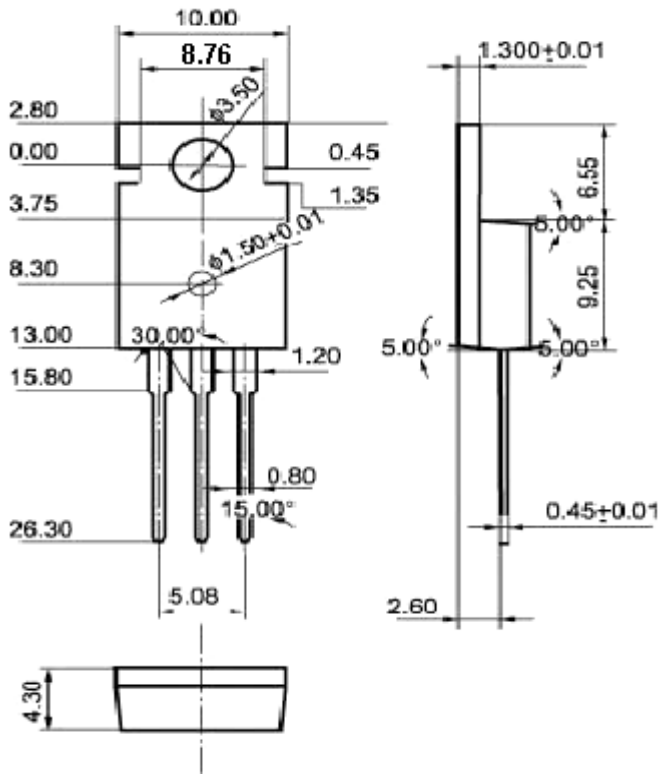

Fig.2 Outline dimensions (unindicated tolerance:±0.10mm)